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# Onsemi

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# Silicon Carbide Schottky Diode

# 650 V, 6 A

# FFSM0665B

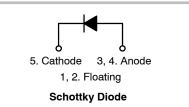
Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

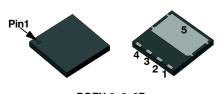


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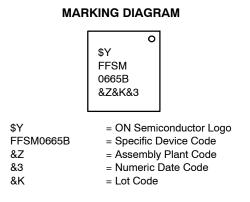
#### www.onsemi.com

V <sub>RRM</sub>	IF
650 V	6.0 A





PQFN 8×8, 2P CASE 483AP



# ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

## • Max Junction Temperature 175°C

- Avalanche Rated 24.5 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### Applications

Features

- General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuits

#### MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise noted)

Parameter	Symbol	Value	Unit		
Peak Repetitive Reverse Voltage	V <sub>RRM</sub>	650	V		
Single Pulse Avalanche Energy (T $I_{L(pk)}$ = 9.9 A, L = 0.5 mH, V = 50	E <sub>AS</sub>	24.5	mJ		
Continuous Rectified Forward	T <sub>C</sub> < 154	١ <sub>F</sub>	6.0	А	
Current	T <sub>C</sub> < 135		9.1		
Non-Repetitive Peak Forward Surge Current	T <sub>C</sub> = 25°C, t <sub>P</sub> = 10 μs	I <sub>FM</sub>	292	A	
	$\begin{array}{l} T_{C} = 150^{\circ}C, \\ t_{P} = 10 \ \mu s \end{array}$		262		
Non-Repetitive Forward Surge Current (Half-Sine Pulse)	T <sub>C</sub> = 25°C t <sub>P</sub> = 8.3 ms	I <sub>FSM</sub>	28	A	
Power Dissipation	T <sub>C</sub> = 25°C	P <sub>tot</sub>	75	W	
	T <sub>C</sub> = 150°C		12.5		
Operating Junction and Storage T Range	T <sub>J</sub> , T <sub>stg</sub>	–55 to +175	°C		

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL RESISTANCE

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	2.0	°C/W

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#### **ELECTRICAL CHARACTERISTICS** (T<sub>J</sub> = $25^{\circ}$ C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
ON CHARACT	ERISTICS					
V <sub>F</sub>	Forward Voltage	$I_F = 6.0 \text{ A}, \text{ T}_J = 25^{\circ}\text{C}$		1.43	1.7	V
		$I_F = 6.0 \text{ A}, \text{ T}_J = 125^{\circ}\text{C}$		1.62		
		I <sub>F</sub> = 6.0 A, T <sub>J</sub> = 175°C		1.69		
I <sub>R</sub> Reverse Current	Reverse Current	$V_R$ = 650 V, $T_J$ = 25°C		0.5	40	μΑ
		$V_{R} = 650 \text{ V}, \text{ T}_{J} = 125^{\circ}\text{C}$		1.0	80	
		V <sub>R</sub> = 650 V, T <sub>J</sub> = 175°C		2.0	160	

#### **CHARGES, CAPACITANCES & GATE RESISTANCE**

Q <sub>C</sub>	Total Capacitive Charge	V <sub>C</sub> = 400 V	16	nC
C <sub>tot</sub>		V <sub>R</sub> = 1 V, f = 100 kHz	259	pF
		V <sub>R</sub> = 200 V, f = 100 kHz	29	
		V <sub>R</sub> = 400 V, f = 100 kHz	22	

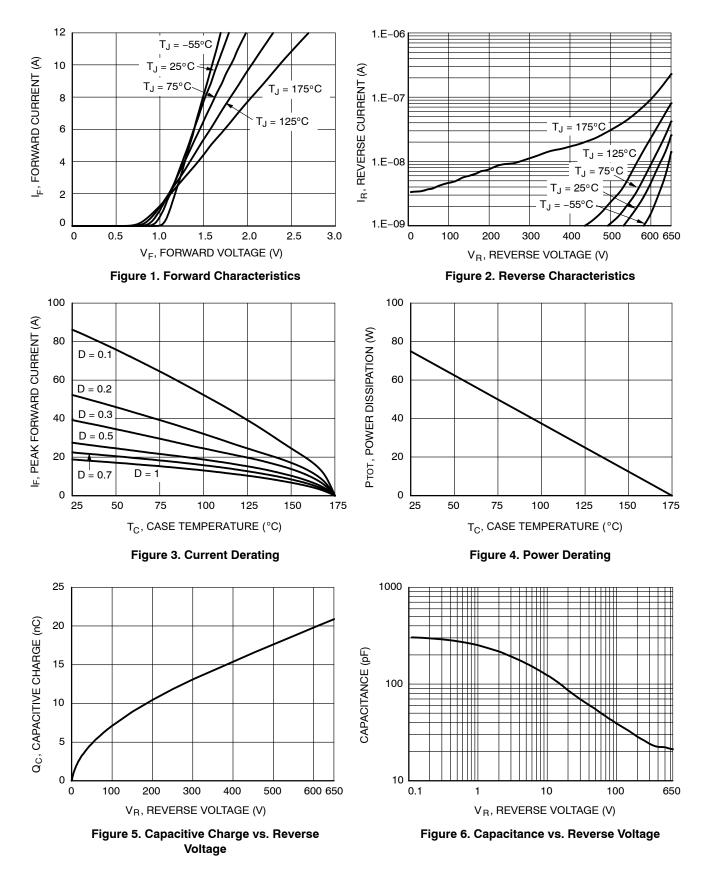
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

#### PART MARKING AND ORDERING INFORMATION

Part Number	Top Mark	Package	Packing Method $^{\dagger}$	Quantity
FFSM0665B	FFSM0665B	PQFN 8X8, 2P (Halogen Free)	Tape & Reel	3000 units

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.





**TYPICAL CHARACTERISTICS** ( $T_J = 25^{\circ}C$  unless otherwise noted)

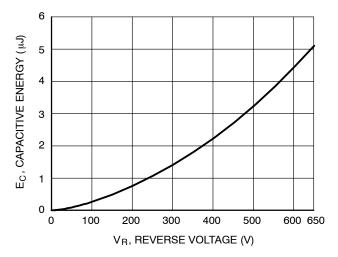
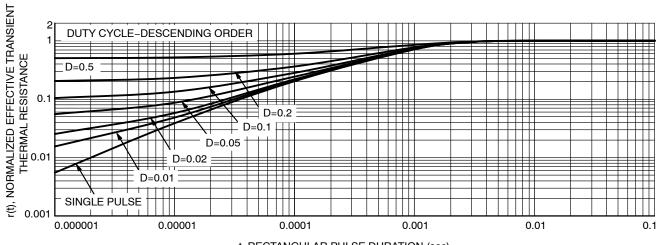


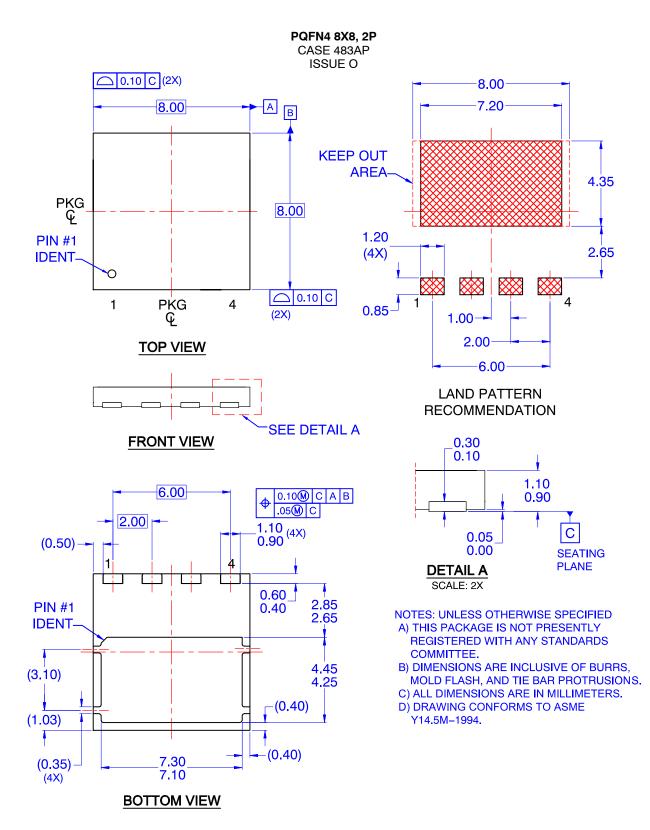
Figure 7. Capacitance Stored Energy



t, RECTANGULAR PULSE DURATION (sec)

Figure 8. Junction-to-Case Transient Thermal Response

#### PACKAGE DIMENSIONS



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